a current blocking layer, formed on said second conductivity type cladding layer around said ridge portion, containing Al as a group III element in this order, wherein

an angle θ of inclination on a side surface of said ridge portion with respect to an upper surface of said substrate is at least 70° and not more than 117°,

a distance t between said emission layer and said current blocking layer satisfies a relation of t £ 0.275/(1 - (X2-X1)) micrometer assuming that X1 represents a composition ratio of Al in group III elements forming said second conductivity type cladding layer, X2 represents a composition ratio of Al in group III elements forming said current blocking layer, and

a lower width W of said ridge portion is at least 2 μm and not more than 5 μm.

A1 (concl)

2. **(Amended)** A semiconductor laser device according to claim 1, wherein

said first conductivity type cladding layer contains Al and Ga as group III elements, and X1 represents a composition ratio of Al in a sum of a contents of Al and Ga, and

said current blocking layer contains Al and Ga, and III elements, and X2 represents the composition ratio of Al in the sum of a contents of Al and Ga.

A2 sub B2

4. **(Amended)** The semiconductor laser device according to claim 1, wherein

said distance t between said emission layer and said current blocking layer satisfies a relation of t £ 0.252/(1 - (X2-X1)) micrometer.

5. (Amended) The semiconductor laser device according to claim 1, wherein said distance t between said emission layer and said current blocking layer is at least 0.15 μm.

A2 (concl.)

6. (Amended) The semiconductor laser device according to claim 1, wherein said distance t between said emission layer and said current blocking layer is at least 0.2 μm.

7. (Amended) The semiconductor laser device according to claim 1, wherein an upper surface of said substrate is a {100} plane or inclined by several degrees, and said ridge portion extends in a <011> direction.